

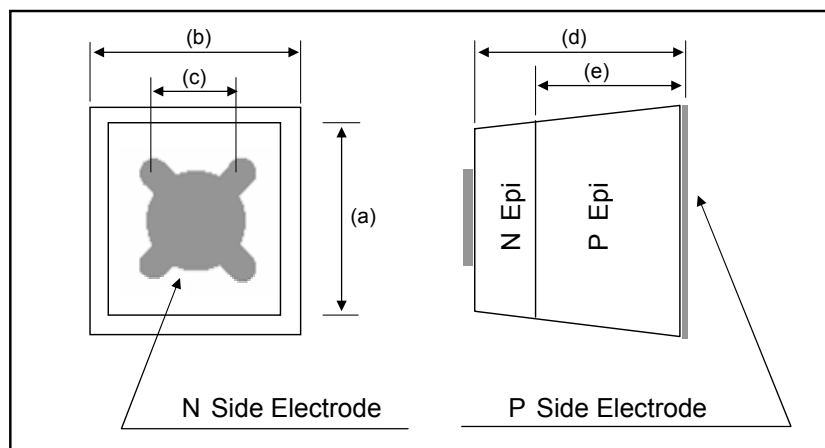
- 1. Material** Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)
- 2. Electrode** N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.8	2	V	IF=100mA
Reverse Voltage	V_R	4			V	IR=10uA
Power	P_O		10.25		mW	IF=100mA
Wavelength	λ_P		880		nm	IF=20mA
	$\Delta\lambda$		80		nm	IF=20mA
Rise Time	Tr		700		ns	
Fall Time	Tf		400		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data**
- (a) Emission Area ----- 10.0mil x 10.0mil
 - (b) Bottom Area ----- 11.0mil x 11.0mil
 - (c) Bonding Pad ----- 110um
 - (d) Chip Thickness ----- 10mil
 - (e) Junction Height ----- 9.0mil



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